Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
300V	40mΩ@10V	70A

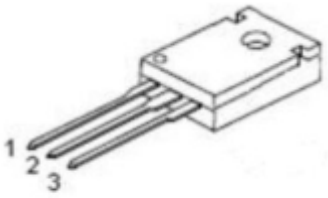
Feature

- Fast Switching
- Low Gate Charge and Rdson
- 100% Single Pulse avalanche energy Test

Applications

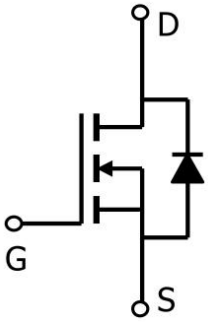
- DC-DC Converter
- Ideal for high-frequency switching and synchronous rectification

Package

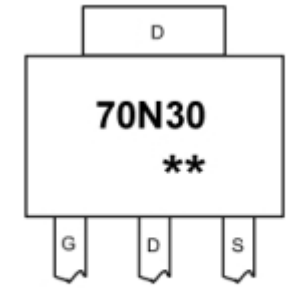


TO-247(1:G 2:D 3:S)

Circuit diagram



Marking



70N30 =Device Code
** =Week Code

Absolute maximum ratings

(T_a=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	300	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current[1](T_C=25℃)	I_D	70	A
Pulsed Drain Current[2]	I_{DM}	280	A
Single Pulse Avalanche Energy[3]	E_{AS}	2795	mJ
Total Power Dissipation(T_C=25℃)	P_D	250	W
Thermal Resistance Junction-Case[1]	$R_{\theta JC}$	0.5	℃/W
Storage Temperature Range	$T_{STG,}$	-55 to 150	℃
Operating Junction Temperature Range	$T_{J,}$	-55 to 150	℃

Electrical characteristics

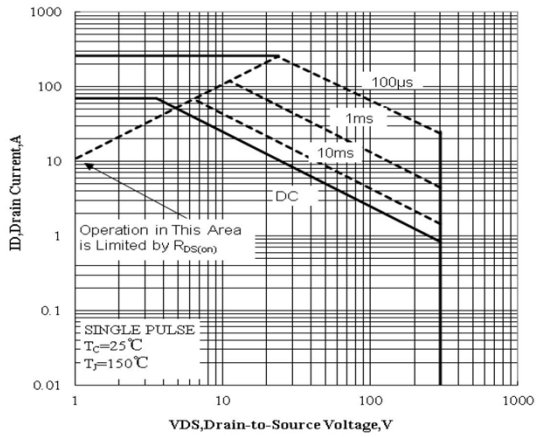
(T_A=25℃, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$BV_{(BR)DSS}$	V_{GS} = 0V, I_D =250μA	300			V
Bvdss Temperature Coefficient	ΔBVDSS/ΔTJ	ID=1mA, Reference25℃		0.3		V/℃
Drain-Source Leakage Current	I_{DSS}	V_{DS} =240V, V_{GS} = 0V			1	uA
Gate-Body Leakage Current	I_{GSS}	V_{GS} =±20V, V_{DS} = 0V			±100	uA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} =V_{GS}, I_D =250μA	2	3	4	V
Static Drain-Source on-Resistance	$R_{DS(on)}$	V_{GS} =10V, I_D =26A		40	50	mΩ
Dynamic Characteristics						
Input capacitance	C_{iss}	V_{DS}=25V, V_{GS}=0V, f=1MHz		8220		pF
Output capacitance	C_{oss}			870		
Reverse transfer capacitance	C_{rss}			106		
Switching Characteristics						
Total Gate Charge	Q_g	V_{DS}=240V, V_{GS}=10V, I_D =69A		136		pF
Gate-Source Charge	Q_{gs}			42.5		
Gate-Drain Charge	Q_{gd}			49		
Turn-on Delay Time	$T_{d(on)}$	V_{DD}=150V, V_{GS}=10V, R_{GEN} =25Ω, I_D =69A		78		nS
Turn-on Rise Time	T_r			307		
Turn-Off Delay Time	$T_{d(off)}$			197		
Turn-Off Fall Time	t_f			140		

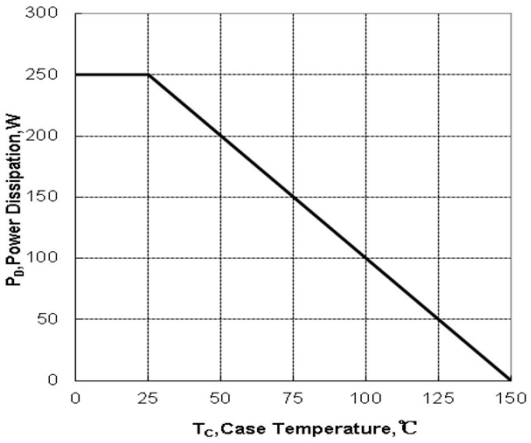
Note：

1. The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper.
2. The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%
3. The EAS data shows Max. rating . The test condition is R_G =30Ω ,L=10mH

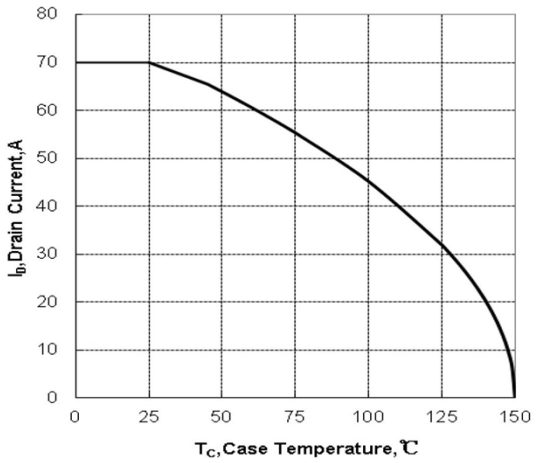
Typical Characteristics



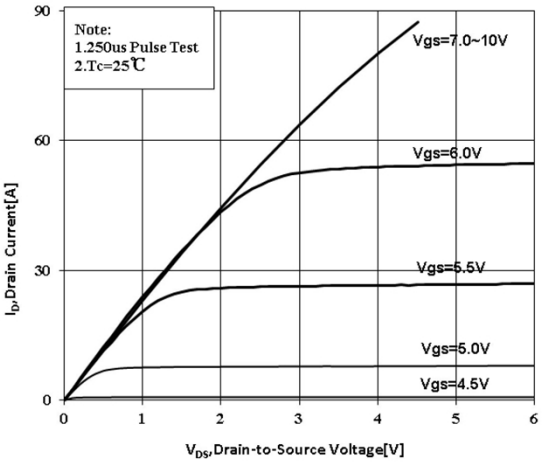
Maximum Forward Bias Safe Operating Area



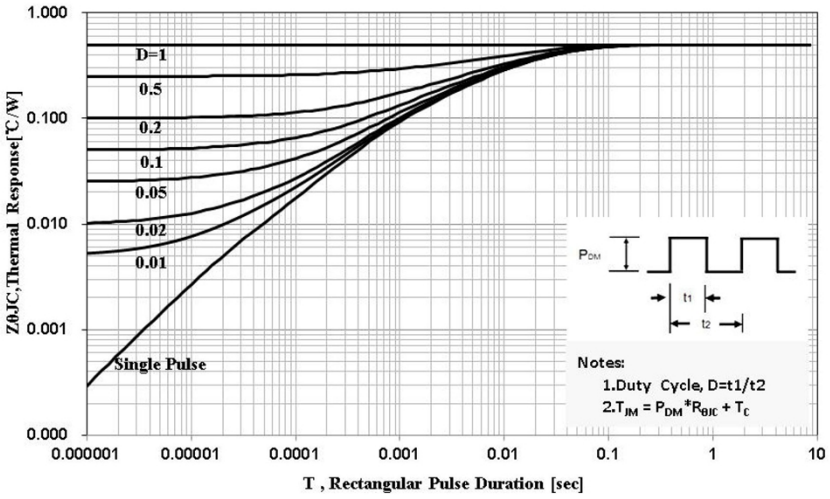
Maximum Power dissipation vs Case Temperature



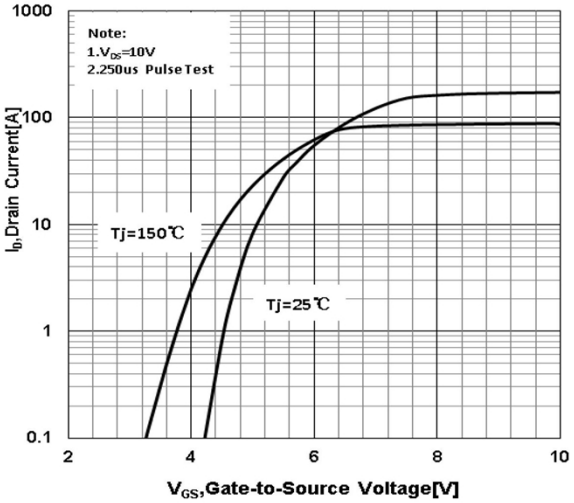
Maximum Continuous Drain Current vs Case Temperature



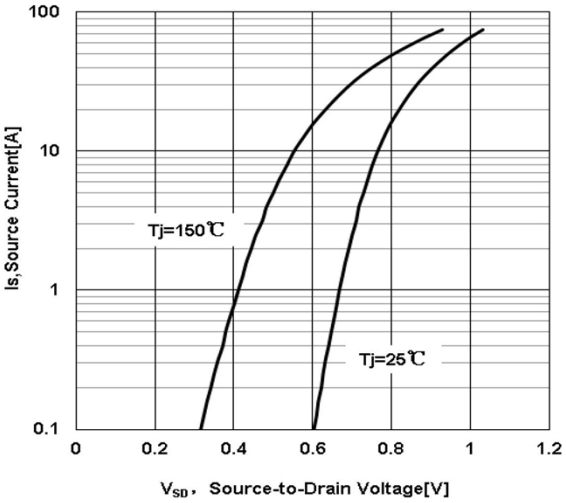
Typical Output Characteristics



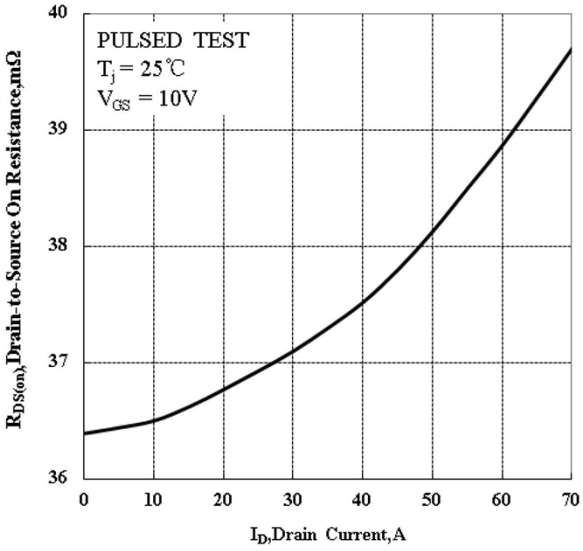
Maximum Effective Thermal Impedance , Junction to Case



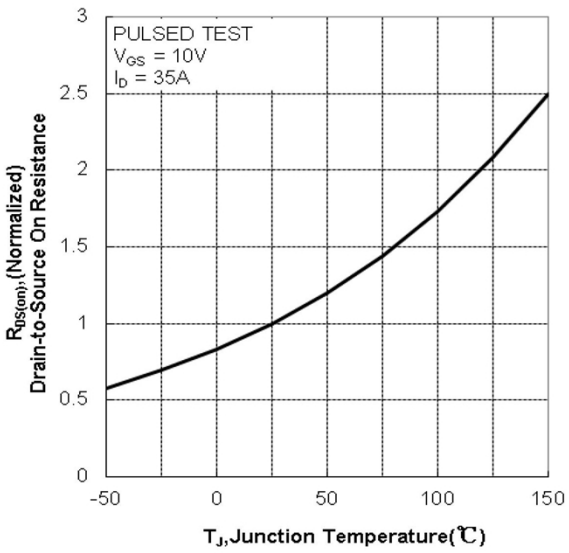
Typical Transfer Characteristics



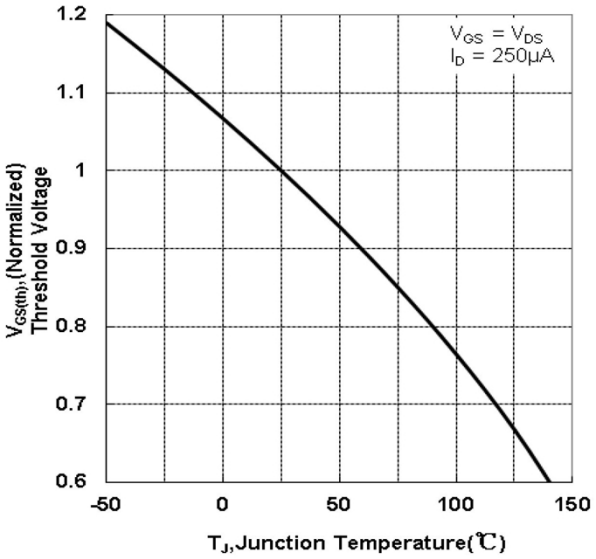
Typical Body Diode Transfer Characteristics



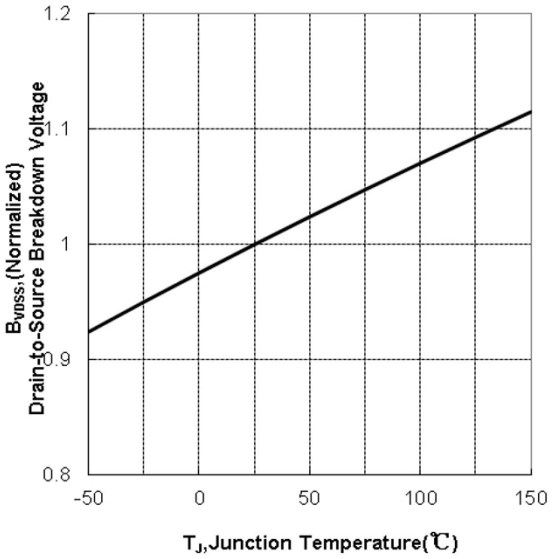
Typical Drain to Source ON Resistance
vs Drain Current



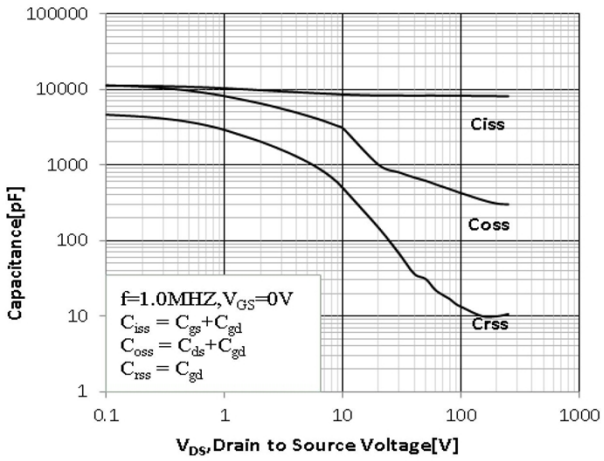
Typical Drian to Source on Resistance
vs Junction Temperature



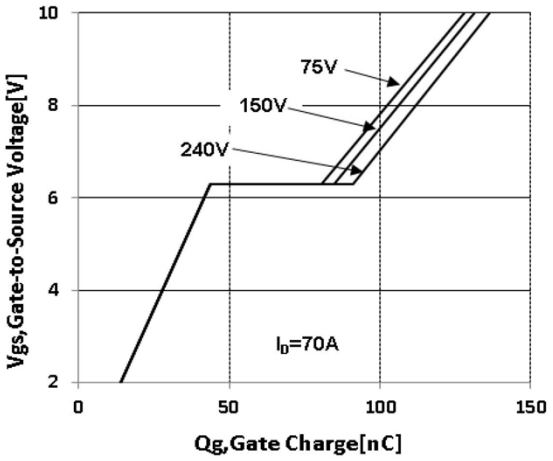
Typical Theshold Voltage vs Junction Temperature



Typical Breakdown Voltage vs Junction Temperature

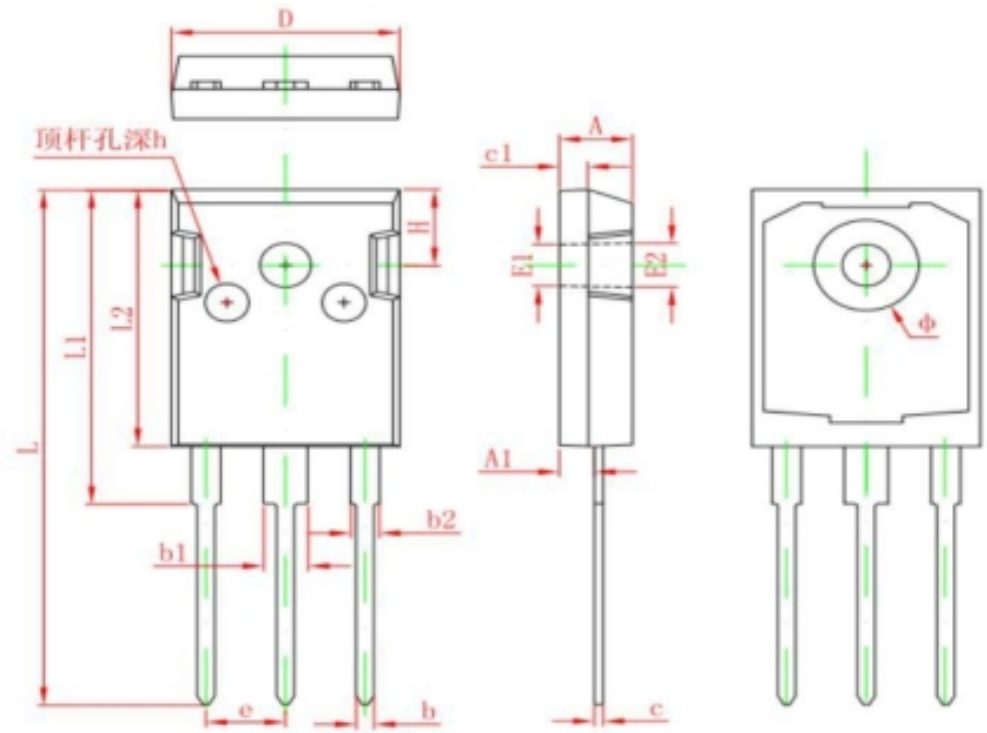


Typical Capacitance vs Drain to Source Voltage



Typical Gate Charge vs Gate to Source Voltage

TO-247 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.850	5.150	0.191	0.200
A1	2.200	2.600	0.087	0.102
b	1.000	1.400	0.039	0.055
b1	2.800	3.200	0.110	0.126
b2	1.800	2.200	0.071	0.087
c	0.500	0.700	0.020	0.028
c1	1.900	2.100	0.075	0.083
D	15.450	15.750	0.608	0.620
E1	3.500 REF.		0.138 REF.	
E2	3.600 REF.		0.142 REF.	
L	40.900	41.300	1.610	1.626
L1	24.800	25.100	0.976	0.988
L2	20.300	20.600	0.799	0.811
Φ	7.100	7.300	0.280	0.287
e	5.450 TYP.		0.215 TYP.	
H	5.980 REF.		0.235 REF.	
h	0.000	0.300	0.000	0.012